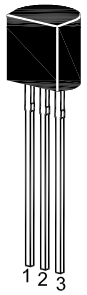
ST 2N6517

NPN Silicon Epitaxial Planar Transistor

for switching and AF amplifier applications.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Base 3. Collector
TO-92 Plastic Package

Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	350	V
Collector Emitter Voltage	V_{CEO}	350	V
Emitter Base Voltage	V_{EBO}	6	V
Collector Current	I_C	500	mA
Power Dissipation	P_{tot}	625	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	- 55 to + 150	°C

Characteristics at T_a = 25 °C

Parameter	Symbol	Min.	Max.	Unit
DC Current Gain				
at V_{CE} = 10 V, I_C = 1 mA	h_{FE}	20	-	-
at V_{CE} = 10 V, I_C = 10 mA	h_{FE}	30	-	-
at V_{CE} = 10 V, I_C = 30 mA	h_{FE}	30	200	-
at V_{CE} = 10 V, I_C = 50 mA	h_{FE}	20	200	-
at V_{CE} = 10 V, I_C = 100 mA	h_{FE}	15	-	-
Collector Base Cutoff Current at V_{CB} = 250 V	I_{CBO}	-	50	nA
Emitter Base Cutoff Current at V_{EB} = 5 V	I_{EBO}	-	50	nA
Collector Base Breakdown Voltage at I_C = 100 µA	$V_{(BR)CBO}$	350	-	V
Collector Emitter Breakdown Voltage at I_C = 1 mA	$V_{(BR)CEO}$	350	-	V
Emitter Base Breakdown Voltage at I_E = 10 µA	$V_{(BR)EBO}$	6	-	V
Collector Emitter Saturation Voltage				
at I_C = 10 mA, I_B = 1 mA	$V_{CE(sat)}$	-	0.3	V
at I_C = 20 mA, I_B = 2 mA	$V_{CE(sat)}$	-	0.35	V
at I_C = 30 mA, I_B = 3 mA	$V_{CE(sat)}$	-	0.5	V
at I_C = 50 mA, I_B = 5 mA	$V_{CE(sat)}$	-	1	V
Base Emitter Saturation Voltage				
at I_C = 10 mA, I_B = 1 mA	$V_{BE(sat)}$	-	0.75	V
at I_C = 20 mA, I_B = 2 mA	$V_{BE(sat)}$	-	0.85	V
at I_C = 30 mA, I_B = 3 mA	$V_{BE(sat)}$	-	0.9	V
Base Emitter On Voltage at V_{CE} = 10 V, I_C = 100 mA	$V_{BE(on)}$	-	2	V
Gain Bandwidth Product at V_{CE} = 20 V, I_C = 10 mA, f = 20 MHz	f_T	40	200	MHz
Collector Base Capacitance at V_{CB} = 20 V, f = 1 MHz	C_{cb}	-	6	pF